

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended): A semiconductor device, comprising:
 - a source region formed of a semiconductor;
 - a drain region formed of a semiconductor of the same conductive type as that of said source region;
 - a channel region formed of a semiconductor between said source region and said drain region;
 - a gate insulating film provided on said channel region; and
 - a gate electrode provided on said gate insulating film and formed with a P-N junction including a P-type semiconductor region and an N-type semiconductor region,
wherein said P-type semiconductor region and said N-type semiconductor region of said P-N junction of said gate electrode are electrically insulated on all sides,
wherein said gate electrode includes a first gate portion provided above said channel region and a second gate portion provided ~~above a region which is not in the semiconductor device~~
~~overlying outside of a region which consists of~~ said channel region, said source region [[or]] and said drain region, and said second gate portion includes said P-N junction.

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2. (original): The semiconductor device according to claim 1,
wherein silicide is not formed on said P-N junction of said gate electrode.

3. (original): The semiconductor device according to claim 1,
wherein said P-N junction of said gate electrode is covered with an insulating material.

4. (original): The semiconductor device according to claim 3,
wherein silicide is formed on a part of said gate electrode which is not covered with said insulating material.

5. (canceled)

6. (previously presented): The semiconductor device according to claim 1, further comprising;

a body region formed of a semiconductor under said channel region;
a buried insulating film provided under said body region, said source region, and said drain region; and

a semiconductor substrate region provided under said buried insulating film.

7. (original): The semiconductor device according to claim 1,
wherein silicide is formed on surfaces of said source region and said drain region.

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8. (original): The semiconductor device according to claim 6, further comprising;
a body contact region formed within said body region and having a higher impurity
concentration than said body region.

9. (original): The semiconductor device according to claim 8,
wherein said body contact region is formed in a region outside said second gate portion.

10-12. (canceled)